VS-HFA04SD60SHM3

Vishay Semiconductors

HEXFRED[®], Ultrafast Soft Recovery Diode, 4 A



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| D-PAK (T | O-252AA |
|----------|---------|
|----------|---------|

| | ○ 2, 4 ▲ |
|-----|-------------|
| 0 1 | 0 3 |
| N/C | Anode |

| PRODUCT SUMMARY | | | | | |
|----------------------------------|------------------|--|--|--|--|
| Package | TO-252AA (D-PAK) | | | | |
| I _{F(AV)} | 4 A | | | | |
| V _R | 600 V | | | | |
| V _F at I _F | 1.8 V | | | | |
| t _{rr} typ. | 17 ns | | | | |
| T _J max. | 150 °C | | | | |
| Diode variation | Single die | | | | |

FEATURES

- Ultrafast recovery time
- Ultrasoft recovery
 Very low I_{RRM}
- Very low I_{RR}
 Very low Q_{rr}
- Guaranteed avalanche
- Specified at operating temperature
- AEC-Q101 gualified
- Meets JESD 201 class 2 whisker test
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION/APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

| ABSOLUTE MAXIMUM RATINGS | | | | |
|---|-----------------------------------|-------------------------|-------------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Cathode to anode voltage | V _{RRM} | | 600 | V |
| Maximum continuous forward current | I _{F(AV)} | T _C = 100 °C | 4 | |
| Single pulse forward current | I _{FSM} | | 25 | A |
| Repetitive peak forward current | I _{FRM} | T _C = 116 °C | 16 | |
| Maximum power dissipation | PD | T _C = 100 °C | 10 | W |
| Operating junction and storage temperatures | T _J , T _{Stg} | | - 55 to 150 | °C |

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | |
|--|-------------------------------------|--|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Breakdown voltage, blocking voltage | V _{BR} , V _R | I _R = 100 μA | 600 | - | - | |
| | | $I_F = 4 A$ | - | 1.5 | 1.8 | V |
| Forward voltage See fig. 1 | V _F | I _F = 8 A | - | 1.8 | 2.2 | |
| See lig. 1 | | I _F = 4 A, T _J = 125 °C | - | 1.4 | 1.7 | |
| Maximum reverse | | $V_{R} = V_{R}$ rated | - | 0.17 | 3.0 | |
| leakage current | IR | $T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$ | - | 44 | 300 | μA |
| Junction capacitance | CT | V _R = 200 V | - | 4 | 8 | pF |
| Series inductance | L _S | Measured lead to lead 5 mm from package body | - | 8.0 | - | nH |

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| DYNAMIC RECOVERY CHARACTERISTICS ($T_C = 25$ °C unless otherwise specified) | | | | | | | | |
|---|--------------------------|---|---------------------------------|--|------|------|---------|---|
| PARAMETER | SYMBOL | TEST CO | NDITIONS | MIN. | TYP. | MAX. | UNITS | |
| | | $I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$ | 200 A/µA, V _R = 30 V | - | 17 | - | | |
| Reverse recovery time | t _{rr} | T _J = 25 °C | | - | 28 | 42 | ns | |
| | | T _J = 125 °C | | - | 38 | 57 | | |
| Deels receivers a unreet | I _{RRM} | T _J = 25 °C | | - | 2.9 | 5.2 | • | |
| Peak recovery current | | IRRM | T _J = 125 °C | I _F = 4 A dI _F /dt = 200 A/μs | - | 3.7 | 6.7 | A |
| | Q _{rr} | T _J = 25 °C | $V_{\rm R} = 200 \text{ V}$ | - | 40 | 60 | nC | |
| Reverse recovery charge | | Qrr | T _J = 125 °C | | - | 70 | 105 | |
| | | T _J = 25 °C | | - | 280 | - | A // 10 | |
| Rate of fall of recovery current | dl _{(rec)M} /dt | T _J = 125 °C | | - | 235 | - | A∕µs | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | |
|--|-----------------------------------|----------------------|--------------|-------|------------|------------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | - 55 | - | 150 | °C |
| Thermal resistance, junction to case | R _{thJC} | | - | - | 5.0 | °C/W |
| Thermal resistance, junction to ambient | R _{thJA} | Typical socket mount | - | - | 80 | 0/11 |
| Weight | | | - | 2.0 | - | g |
| weight | | | - | 0.07 | - | oz. |
| Mounting torque | | | 6.0 (5.0) | - | 12 (10) | kgf · cm (lbf · in) |
| Marking device | | Case style D-PAK | | HFA04 | SD60SH | |

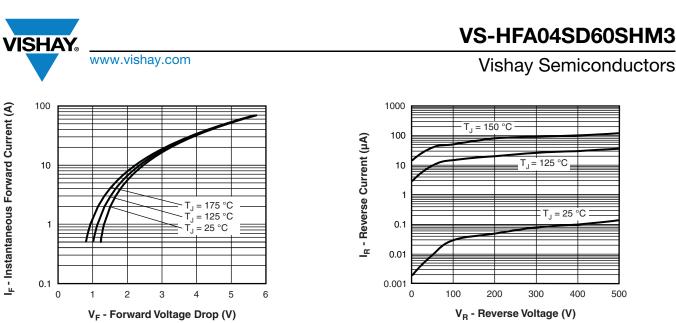


Fig. 1 - Typical Forward Voltage Drop Characteristics

Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

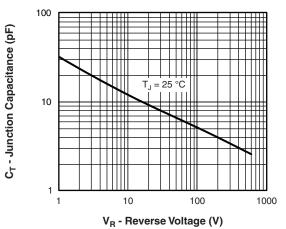
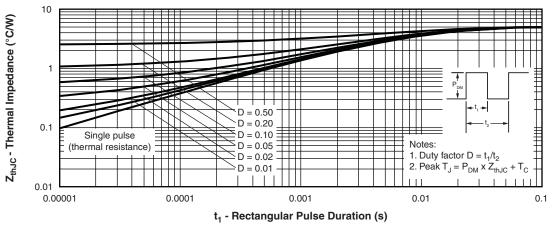
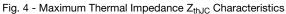


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





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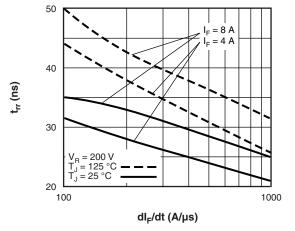
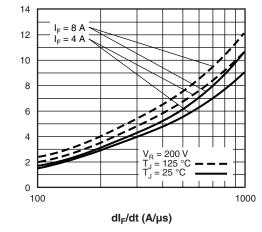


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

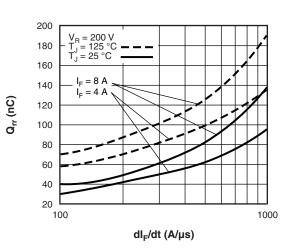


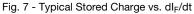
I_{RR} (A)

Fig. 6 - Typical Recovery Current vs. dl_F/dt

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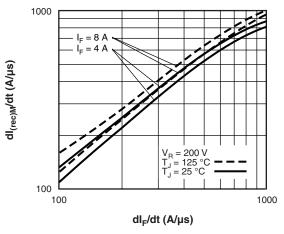


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt

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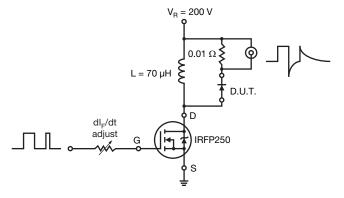
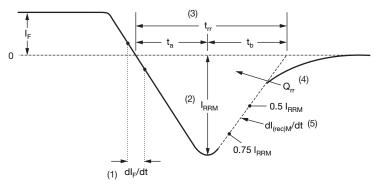


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (5) dl_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}

 $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$

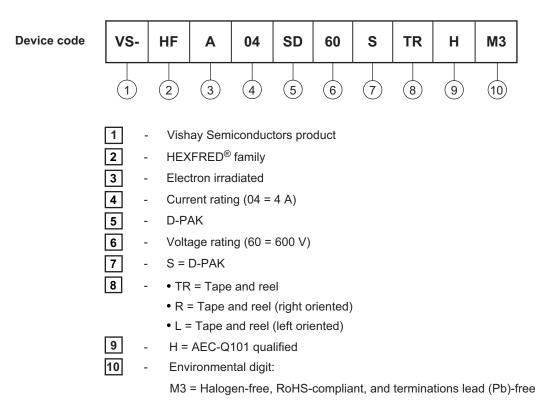
Fig. 10 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE

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| ORDERING INFORMATION (Example) | | | | | |
|--------------------------------|------------------|------------------------|-------------------------|--|--|
| PREFERRED P/N | QUANTITY PER T/R | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION | | |
| VS-HFA04SD60SHM3 | 75 | 3000 | Antistatic plastic tube | | |
| VS-HFA04SD60STRHM3 | 2000 | 2000 | 13" diameter reel | | |
| VS-HFA04SD60STRRHM3 | 3000 | 3000 | 13" diameter reel | | |
| VS-HFA04SD60STRLHM3 | 3000 | 3000 | 13" diameter reel | | |

| LINKS TO RELATED DOCUMENTS | | | | |
|-------------------------------------|--------------------------|--|--|--|
| Dimensions www.vishay.com/doc?95519 | | | | |
| Part marking information | www.vishay.com/doc?95518 | | | |
| Packaging information | www.vishay.com/doc?95033 | | | |

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